

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI HF75-28F** is Designed for

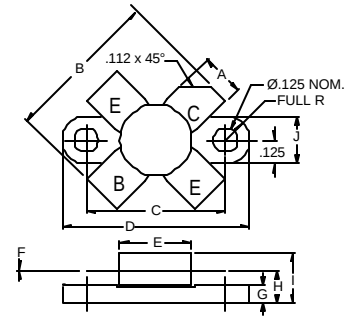
FEATURES:

- $P_G = 18$ dB min. at 75 W/30 MHz
- $IMD_3 = -30$ dBc max. at 75 W (PEP)
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	10 A
V_{CB}	60 V
V_{CE}	35 V
P_{DISS}	140 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
q_{JC}	1.05 $^\circ C/W$

PACKAGE STYLE .380 4L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

ORDER CODE: ASI10606

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA	35			V
BV_{CER}	$I_C = 50$ mA $R_{BE} = 10 \Omega$	60			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CES}	$V_E = 28$ V			5	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ A	10		100	---
C_{ob}	$V_{CB} = 28$ V $f = 1.0$ MHz			80	pF
G_{PE}	$V_{CE} = 25$ V $I_{CQ} = 3.2$ A $f = 225$ MHz	13.5	14.5		dB
IMD_3	$P_{REF} = 16$ W Vision = -8 dB Side Band = -16 dB Snd. = -7 dB			-55	dBc